METHOD OF MANUFACTURING SOI SUBSTRATE

ABSTRACT OF THE DISCLOSURE

An object of the present invention is to improve use efficiency of a semiconductor substrate without lowering efficiency of a fabrication process. Another object of the present invention is to achieve cost reduction by effective use of a semiconductor substrate whose thickness is reduced due to repeated use in a process of manufacturing an SOI substrate. In a process of manufacturing an SOI substrate, a semiconductor substrate is used as a bond substrate a predetermined number of times, or as long as it meets predetermined conditions. In a case where a first single crystal semiconductor substrate cannot be used as a bond substrate, it is bonded to a second single crystal semiconductor substrate. Then, a stacked-layer substrate formed from the first single crystal semiconductor substrate and the second single crystal semiconductor substrate bonded to each other is used as a bond substrate in a process of manufacturing an SOI substrate.

Figure 6D